



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
40V	3.6mΩ @ V _{GS} = 10V	100A
	5.2mΩ @ V _{GS} = 5V	90A

Features


- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} – Ensures On State Losses are Minimized
- Excellent Q_{gd} x R_{DS(ON)} Product (FOM)

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Power Management Functions
- DC-DC Converters
- Backlighting

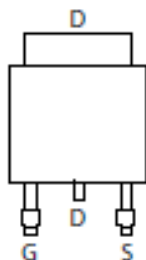
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 
- Weight: 0.33 grams (Approximate)

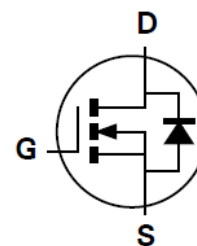
TO252 (DPAK)



Top View



Pin Out Top View



Equivalent Circuit

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DS}	40	V	
Gate-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 6)	I_D	$T_A = +25^\circ\text{C}$ $T_A = +100^\circ\text{C}$	17.6 12.5	A
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 7)		$T_C = +25^\circ\text{C}$ $T_C = +100^\circ\text{C}$	100 80	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	150	A	
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	70	A	
Pulsed Body Diode Forward Current (10 μs Pulse, Duty Cycle = 1%)	I_{SM}	150	A	
Avalanche Current, $L=1\text{mH}$	I_{AS}	13.2	A	
Avalanche Energy, $L=1\text{mH}$	E_{AS}	87	mJ	

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_D	3.1	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	47	$^\circ\text{C/W}$
Total Power Dissipation (Note 7)	P_D	88	W
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	1.7	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	$V_{GS} = 0\text{V}, I_D = 1\text{mA}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 32\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	2.9	3.6	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	4.3	5.2	$\text{m}\Omega$	$V_{GS} = 5\text{V}, I_D = 15\text{A}$
Diode Forward Voltage	V_{SD}	—	—	1.2	V	$V_{GS} = 0\text{V}, I_S = 20\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	2,693	—	pF	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	1,172	—		
Reverse Transfer Capacitance	C_{rss}	—	52	—		
Gate Resistance	R_g	—	2.54	—	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	38.5	—	nC	$V_{DS} = 20\text{V}, I_D = 20\text{A}$
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	17.6	—		
Gate-Source Charge	Q_{gs}	—	6.9	—		
Gate-Drain Charge	Q_{gd}	—	6.9	—		
Turn-On Delay Time	$t_{D(ON)}$	—	5.2	—	ns	$V_{DD} = 20\text{V}, V_{GS} = 10\text{V}, I_D = 20\text{A}, R_G = 1.6\Omega$
Turn-On Rise Time	t_R	—	5.7	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	23.5	—		
Turn-Off Fall Time	t_F	—	11	—		
Body Diode Reverse Recovery Time	t_{RR}	—	35.4	—	ns	$I_F = 15\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{RR}	—	32.9	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

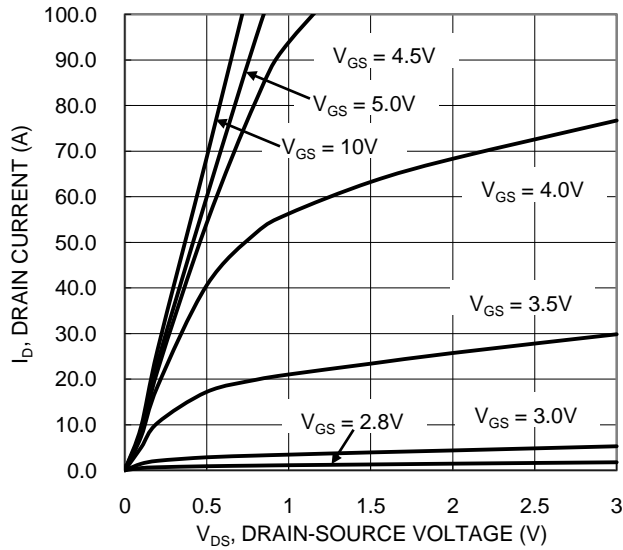


Figure 1. Typical Output Characteristic

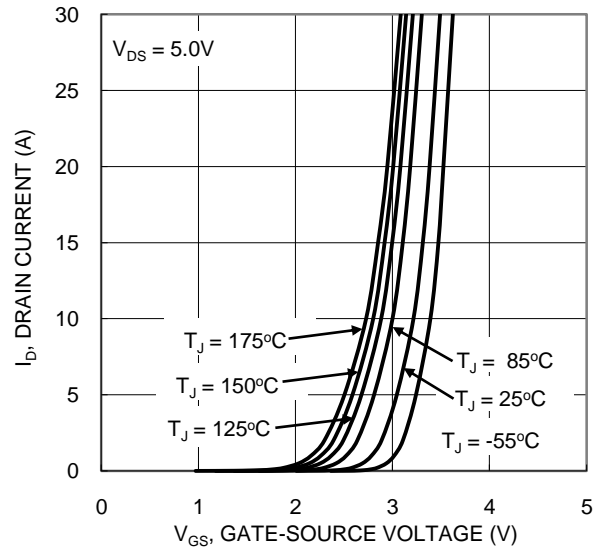


Figure 2. Typical Transfer Characteristic

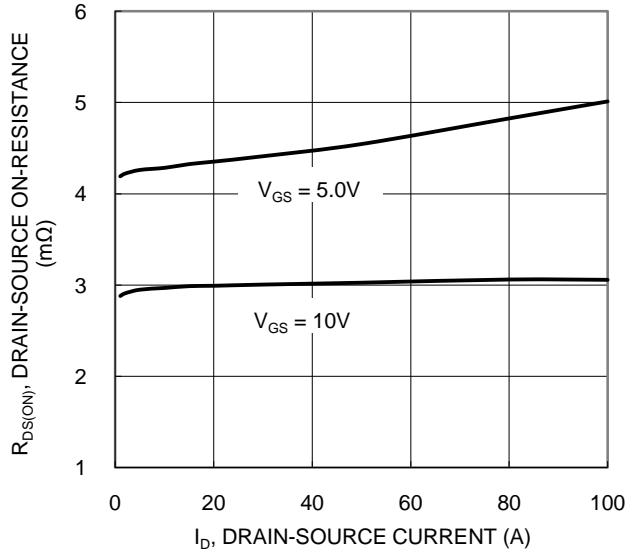


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

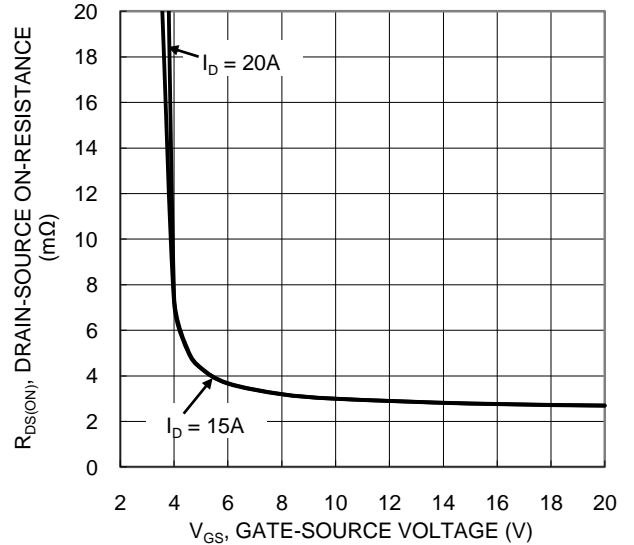


Figure 4. Typical Transfer Characteristic

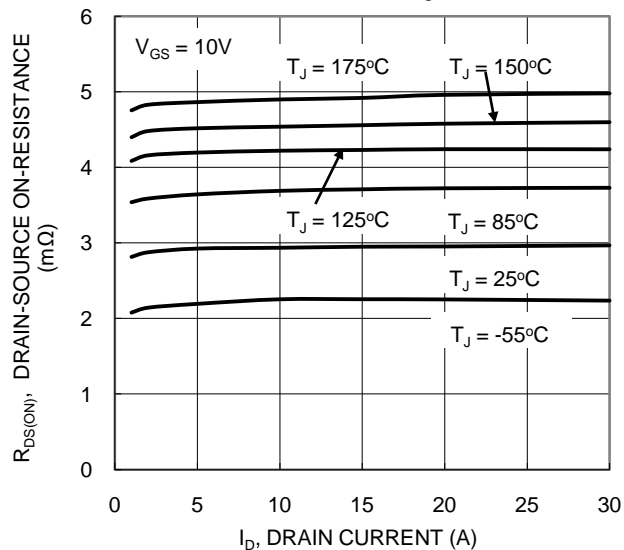


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

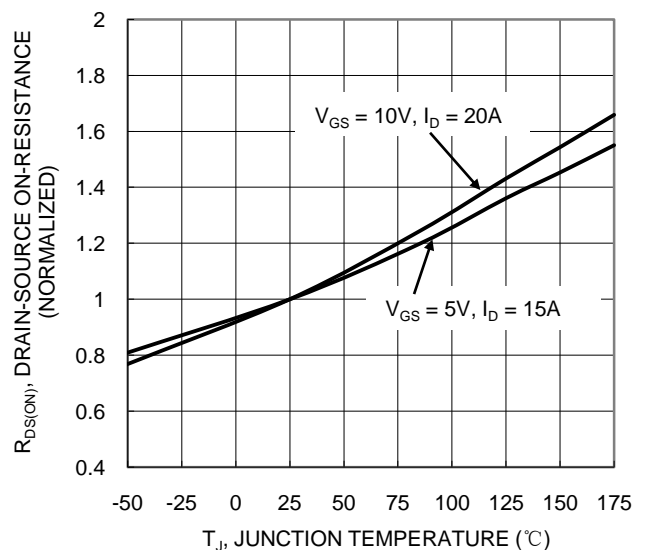


Figure 6. On-Resistance Variation with Temperature

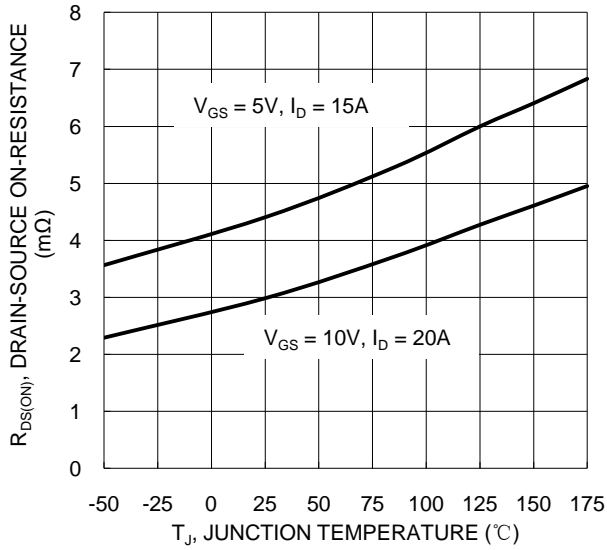


Figure 7. On-Resistance Variation with Temperature

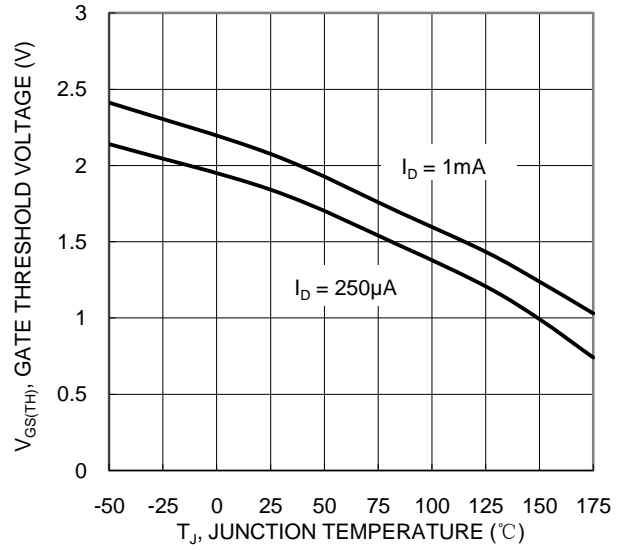


Figure 8. Gate Threshold Variation vs. Junction Temperature

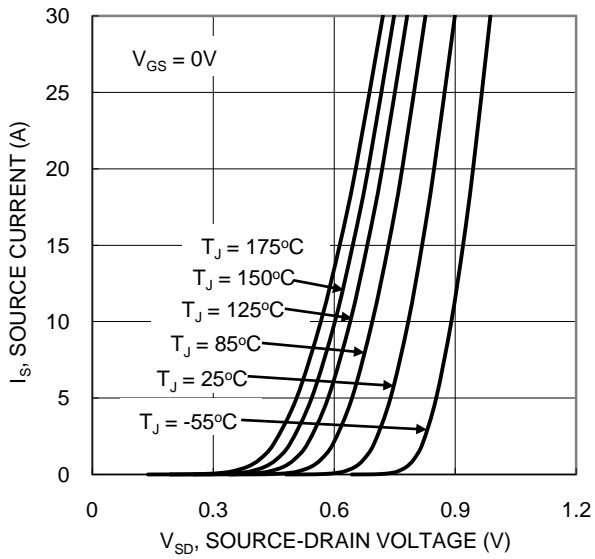


Figure 9. Diode Forward Voltage vs. Current

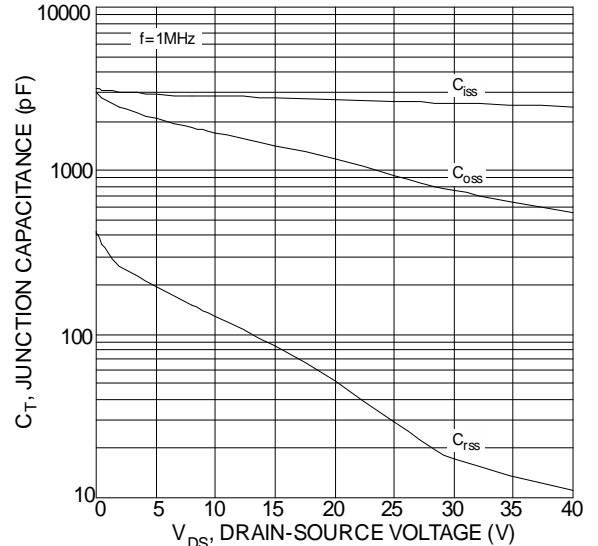


Figure 10. Typical Junction Capacitance

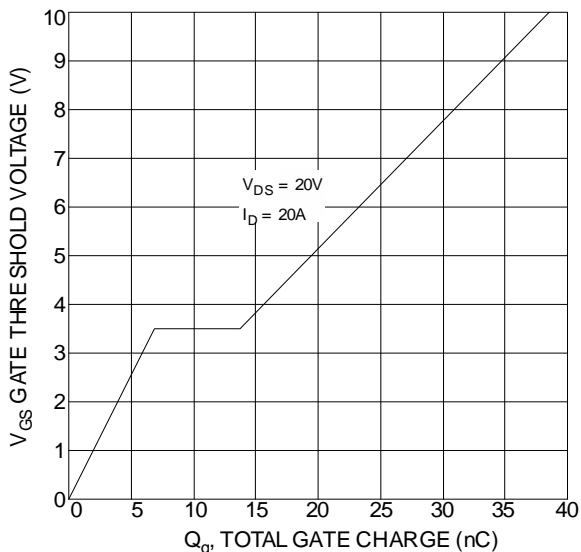


Figure 11. Gate Charge

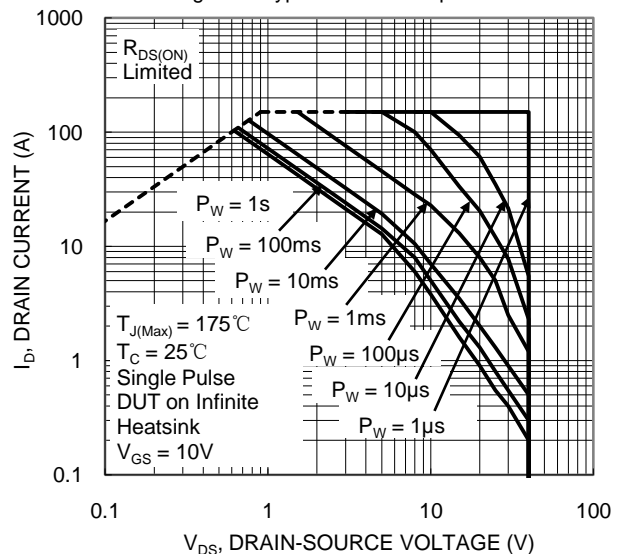


Figure 12. SOA, Safe Operation Area

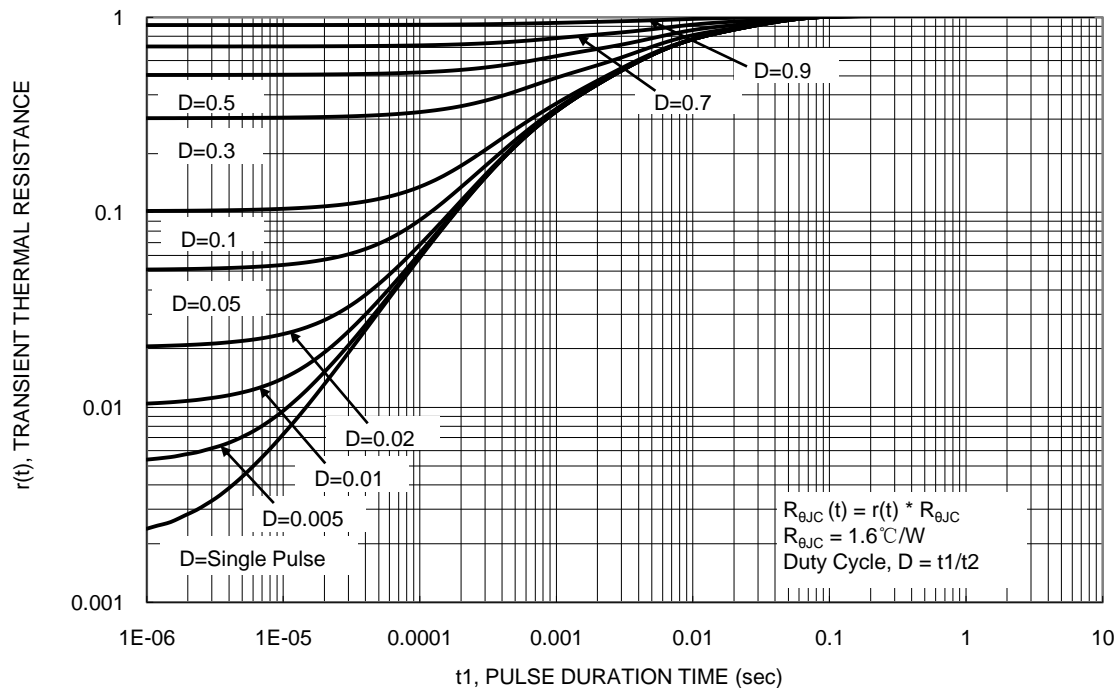
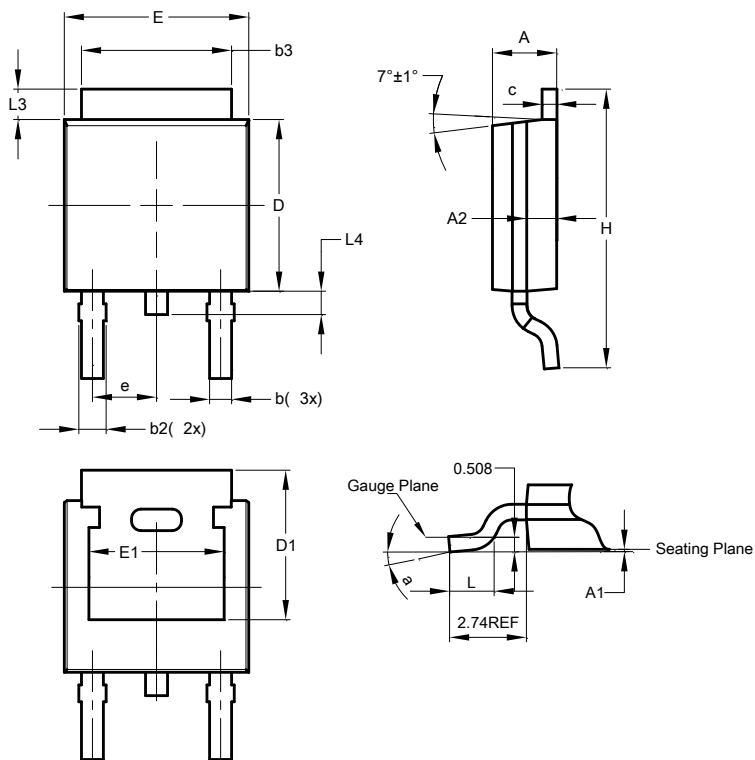


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

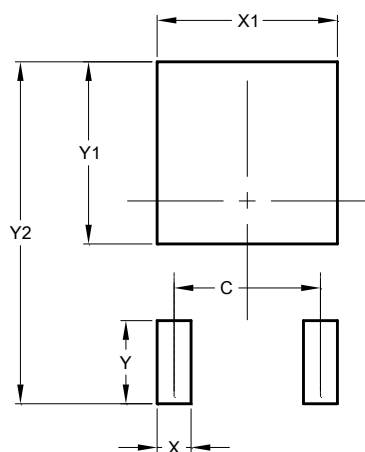
TO252 (DPAK)



TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700